Journal of Crystal Growth 129 (1993) 795–800
North-Holland

JOURNAL OF CRYSTAL GROWTH

Author index

Agarwal, M.K., P.D. Patel and S.K. Gupta, Effect of doping $MoSe_2$ single crystals with rhenium 129 (1993) 559
Angelier, B., see Rouzaud 129 (1993) 173
Armas, B., see Aspar 129 (1993) 56
Aspar, B., R. Rodríguez-Clemente, A. Figueras, B. Armas and C. Combescure, Influence of the experimental conditions on the morphology of CVD AlN films 129 (1993) 56
Ausloos, M., see Cloots 129 (1993) 394
Azéma, N., see Meng 129 (1993) 610
Azéma, N., J. Durand, R. Berjoan, C. Dupuy, J.L. Balladore and L. Cot, Plasma-enhanced chemical vapour deposition of AlN $(10\bar{1}0)$ on Si (100): microstructural study of the interlayers 129 (1993) 621

Balladore, J.L., see Azéma 129 (1993) 621
Bennema, P., see Cherepanova 129 (1993) 202
Berjoan, R., see Azéma 129 (1993) 621
Bilger, G., see Waag 129 (1993) 243
Blachman, R., see Bordui 129 (1993) 371
Boeck, T., C. Frank, H. Günther and K. Jacobs, Indium doping of $Hg_{1-x}Cd_xTe$ grown by liquid phase epitaxy 129 (1993) 233
Bordui, P.F., G.D. Calvert and R. Blachman, Immersion-seeded growth of large barium borate crystals from sodium chloride solution 129 (1993) 371
Brès, E.F., G. Moebus, H.-J. Kleebe, G. Pourroy, J. Werkmann and G. Ehret, High resolution electron microscopy study of amorphous calcium phosphate 129 (1993) 149
Brokman, A., see Vilenkin 129 (1993) 67
Broom, R.F., see Catana 129 (1993) 779
Bryskiewicz, T. and A. Laferrière, Growth of alloy substrates by liquid phase electroepitaxy; theoretical considerations 129 (1993) 429

Calvert, G.D., see Bordui 129 (1993) 371
Camel, D., see Drevet 129 (1993) 549
Casey, N.L., see Huffman 129 (1993) 525
Castaing, J., see Patriarche 129 (1993) 375
Catana, A., R.F. Broom, R. Germann and P. Roentgen, Regrowth of InP by MOVPE on dry-etched heterostructures of InP–GaInAsP 129 (1993) 779
Champness, C.H., see Yip 129 (1993) 102
Champness, C.H., see Shukri 129 (1993) 107
Chang, Ying-Chuan, De-Sen Hou, Yu-De Yu, Si-Shen Xie and Tang Zhou, Color center and domain structure in single crystals of $LaAlO_3$ 129 (1993) 362
Changkang, Chen, Hu Yongle, B.M. Wanklyn and J.W. Hodby, Crystal growth of CuO from BaO flux 129 (1993) 239
Chatillon, C., Critical analysis of the thermodynamic properties of the In–Se gaseous and solid phases 129 (1993) 297
Chatillon, C. and J.-Y. Emery, Thermodynamic analysis of molecular beam epitaxy of compounds in the In–Se system 129 (1993) 312
Chen Changkang, see Changkang 129 (1993) 239
Chen Fangyu, see Kaito 129 (1993) 367
Chen, Nuofu, Ultrasonic etching of GaAs in CrO_3–HF aqueous solutions 129 (1993) 777
Chen Qinggui, see Wang 129 (1993) 774
Chen, Z.H., see Li 129 (1993) 532
Cherepanova, T.A., A.V. Stekolnikov and P. Bennema, Weighted-density functional approach for the solid–liquid interfaces in electrolytes 129 (1993) 202
Cloots, R., A. Rulmont, T. Krekels, G. Van Tendeloo, P. Diko and M. Ausloos, Investigation by electron diffraction microscopy of $(RE)Ba_2Cu_3O_{6+x}S_y$ polycrystalline ceramic compounds: interpretation of unexpected superstructures and influence of secondary phases 129 (1993) 394
Cockayne, B., see Mackey 129 (1993) 269
Cole-Hamilton, D.J., see Yates 129 (1993) 215
Combescure, C., see Aspar 129 (1993) 56
Coméra, J., see Rouzaud 129 (1993) 173
Contamin, P., see Rouzaud 129 (1993) 173
Coriell, S.R., see Murray 129 (1993) 70
Cot, L., see Meng 129 (1993) 610
Cot, L., see Azéma 129 (1993) 621
Crary, S.B., see Sherwin 129 (1993) 794
Cros, B., see Meng 129 (1993) 610
Crosbie, M.J., see Mackey 129 (1993) 269
Cui, S.F., see Li 129 (1993) 532
Cullis, A.G., see Mackey 129 (1993) 269

Dash, J.G., see Elbaum 129 (1993) 491
De Croon, M.H.J.M., see Hageman 129 (1993) 281
Derby, J.J., see Xiao 129 (1993) 593

Diko, P., see Cloots 129 (1993) 394
Dong Qiwei, see Wang 129 (1993) 774
Dong Rongkang, see Wang 129 (1993) 774
Drevet, B., J.P. Garandet, D. Camel and J.J. Favier, Influence of thermal buoyancy on fibrous eutectic growth. I. Segregation results in the Sn–Cu_6Sn_5 system 129 (1993) 549
Dupuy, C., see Azéma 129 (1993) 621
Durand, J., see Meng 129 (1993) 610
Durand, J., see Azéma 129 (1993) 621

Echigoya, J. and S. Hayashi, Directional solidification of CoO–ZrO_2 eutectics 129 (1993) 699
Ehret, G., see Brès 129 (1993) 149
Eichinger, P., see Zimmermann 129 (1993) 582
Elbaum, M., S.G. Lipson and J.G. Dash, Optical study of surface melting on ice 129 (1993) 491
Elta, M.E., see Sherwin 129 (1993) 794
Emel'chenko, G.A., see Zhokhov 129 (1993) 786
Emery, J.-Y., see Chatillon 129 (1993) 312

Favier, J.J., see Rouzaud 129 (1993) 173
Favier, J.J., see Drevet 129 (1993) 549
Figueras, A., see Aspar 129 (1993) 56
Filz, T., see Zimmermann 129 (1993) 37
Frank, C., see Boeck 129 (1993) 233
Fujiyasu, H., see Tatsuoka 129 (1993) 686
Fukuda, T., see Pan 129 (1993) 365
Füredi-Milhofer, H., see Škrtić 129 (1993) 449
Furukawa, Y. and S. Kohata, Temperature dependence of the growth form of negative crystal in an ice single crystal and evaporation kinetics for its surfaces 129 (1993) 571

Gao, D., A.W. Stevenson, S.W. Wilkins and G.N. Pain, Microcracks in a GaAs/Si wafer studied by X-ray diffraction 129 (1993) 134
Garandet, J.P., see Drevet 129 (1993) 549
Garside, J., see Matsuoka 129 (1993) 385
Ge, Peiwen, see Xu 129 (1993) 506
Germann, R., see Catana 129 (1993) 779
Gervais, M., see Pellerin 129 (1993) 21
Giling, L.J., see Hageman 129 (1993) 281
Gimmnich, P., see Zimmermann 129 (1993) 37
Glass, J.T., see Wang 129 (1993) 45
Göbel, E.O., see Zimmermann 129 (1993) 37
Gösele, U., see Zimmermann 129 (1993) 582
Gratz, A.J. and P.E. Hillner, Poisoning of calcite growth viewed in the atomic force microscope (AFM) 129 (1993) 789
Gryaznov, V.G., see Romanov 129 (1993) 691
Günther, H., see Boeck 129 (1993) 233
Gupta, S.K., see Agarwal 129 (1993) 559

Haddad, G.I., see Sherwin 129 (1993) 794
Hageman, P.R., M.H.J.M. de Croon, X. Tang and L.J. Giling, Pressure and temperature dependence of Zn incorporation in metalorganic chemical vapour deposition grown GaAs and AlGaAs using diethylzinc as precursor 129 (1993) 281
Hayashi, S., see Echigoya 129 (1993) 699
Henry, C.R., M. Meunier and S. Morel, Helium diffraction study of the nucleation and growth of palladium clusters on MgO (100) 129 (1993) 416
Herbillon, F., see Rouzaud 129 (1993) 173
Hicks, R.F., see Liu 129 (1993) 111
Hillner, P.E., see Gratz 129 (1993) 789
Hirano, R., see Nakamura 129 (1993) 456
Hochberg, A.K., see Love 129 (1993) 119
Hodby, J.W., see Changkang 129 (1993) 239
Hommel, D., see Waag 129 (1993) 243
Huo, Chongru, see Xu 129 (1993) 506
Hou, De-Sen, see Chang 129 (1993) 362
Howard, S.B., see Rosenberger 129 (1993) 1
Hu Yongle, see Yongle 129 (1993) 239
Huffman, J.E. and N.L. Casey, Growth methods for high purity Ge and Ge:Ga homoepitaxy 129 (1993) 525

Ida, M., K. Kurishima and T. Kobayashi, Selective InGaAs growth at low temperature by metalorganic chemical vapor deposition (MOCVD) with high-speed rotating susceptor 129 (1993) 783
Iga, K., see Uchida 129 (1993) 275
Ikeda, E., see Namamura 129 (1993) 456
Ishihara, T., see Oda 129 (1993) 30
Ishizawa, N., see Tanaka 129 (1993) 683
Ivanov, I., see Yakimova 129 (1993) 143

Jacobs, K., see Boeck 129 (1993) 233
Jones, A.C., Metalorganic precursors for vapour phase epitaxy 129 (1993) 728
Junghanns, T., see Romanov 129 (1993) 691

Kaito, C., Y. Saito, T. Watanabe, A. Matsumoto, K. Ohtsuka and Chen Fangyu, Growth mechanism of tubular ultrafine particles of tin sulfide 129 (1993) 367
Karpov, S.Yu., Yu.V. Kovalchuk, V.E. Myachin and Yu.V. Pogorelskii, Instability of III–V compound surfaces due to liquid phase formation 129 (1993) 563
Katsura, S., see Nakamura 129 (1993) 456
Kiselev, A.N., A.A. Velichko and I.A. Okomelchenko, High-resolution electron microscopy of epitaxial layers and interfaces in the CaF_2/Si (100) and CaF_2/Si/CaF_2/Si (100) heterosystems 129 (1993) 163
Kleebe, H.-J., see Brès 129 (1993) 149
Klemenz, C. and H.J. Scheel, Liquid phase epitaxy of high-T_c superconductors 129 (1993) 421
Kobayashi, T., see Ida 129 (1993) 783
Kohata, S., see Furukawa 129 (1993) 571

Komori, T., see Tanaka 129 (1993) 683
Kovalchuk, Yu.V., see Karpov 129 (1993) 563
Koyama, F., see Uchida 129 (1993) 275
Krämer, V., see Post 129 (1993) 485
Krekels, T., see Cloots 129 (1993) 394
Kubel, F. and H. Schmid, Growth, twinning and etch figures of ferroelectric/ferroelastic dendritic $BiFeO_3$ single domain crystals 129 (1993) 515
Kühne, H. and H. Richter, Control of $Si_{1-x}Ge_x$ growth from the gas phase. I. The effect of the layer source gases 129 (1993) 321
Kurishima, K., see Ida 129 (1993) 783
Kurpas, P., see Zimmermann 129 (1993) 37
Kuwabara, H., see Tatsuoka 129 (1993) 686

Laferrière, A., see Bryskiewicz 129 (1993) 429
Landwehr, G., see Waag 129 (1993) 243
Li, J.H., Z.H. Mai, S.F. Cui, Z.H. Chen and M.H. Li, Characterization of $Al_xGa_{1-x}As/Al_yGa_{1-y}As/GaAs$ step multi-quantum wells on (001) GaAs by X-ray double-crystal diffraction 129 (1993) 532
Li, M.H., see Li 129 (1993) 532
Lipson, S.G., see Elbaum 129 (1993) 491
Liu, B., R.F. Hicks and J.J. Zinck, Reaction engineering of photo-assisted chemical vapor deposition 129 (1993) 111
Lorberth, J., see Zimmermann 129 (1993) 37
Love, A., S. Middleman and A.K. Hochberg, The dynamics of bubblers as vapor delivery systems 129 (1993) 119
Louchev, O.A., The influence of radiative heat transfer on the limit pull rate in Czochralski crystal growth of silicon 129 (1993) 179
Lu, Da-cheng, Growth of wide band gap immiscible II–VI alloys by metalorganic vapor phase epitaxy 129 (1993) 629
Lumley, J.L., see Ristorcelli 129 (1993) 249
Lundström, T., see Okada 129 (1993) 543

Mackey, K.J., G.M. Williams, M.J. Crosbie, A.G. Cullis and B. Cockayne, A study of titanium-doped yttrium orthoaluminate using scanning photoluminescence and low temperature cathodoluminescence 129 (1993) 269
Mai, Z.H., see Li 129 (1993) 532
Makino, N., see Nakamura 129 (1993) 456
Mantovani, G., see Saska 129 (1993) 91
Marfaing, Y., see Patriarche 129 (1993) 375
Marschner, T., see Zimmermann 129 (1993) 37
Marumo, F., see Tanaka 129 (1993) 683
Matsumoto, A., see Kaito 129 (1993) 367
Matsuoka, M. and J. Garside, The significance of mass and heat transfer during crystal growth from solutions and melts 129 (1993) 385
Matyi, R.J., M.R. Melloch and J.M. Woodall, Structural analysis of as-deposited and annealed low-temperature gallium arsenide 129 (1993) 719
McFadden, G.B., see Murray 129 (1993) 70
Melloch, M.R., see Matyi 129 (1993) 719
Meng, G.Y., N. Azéma, B. Cros, J. Durand and L. Cot, The growth mechanism of $\langle 10\bar{1}0 \rangle$ oriented AlN thin films by low-frequency plasma-enhanced metalorganic chemical vapour deposition process 129 (1993) 610
Meunier, M., see Henry 129 (1993) 416
Middleman, S., see Love 129 (1993) 119
Miyamoto, T., see Uchida 129 (1993) 275
Moebus, G., see Brès 129 (1993) 149
Monaco, L.A. and F. Rosenberger, Growth and etching kinetics of tetragonal lysozyme 129 (1993) 465
Morel, S., see Henry 129 (1993) 416
Mori, H., see Takagishi 129 (1993) 443
Moriya, K., see Wada 129 (1993) 405
Munns, G.O., see Sherwin 129 (1993) 794
Murray, B.T., S.R. Coriell, G.B. McFadden, A.A. Wheeler and B.V. Saunders, Gravitational modulation of thermosolutal convection during directional solidification 129 (1993) 70
Myachin, V.E., see Karpov 129 (1993) 563

Nakadate, S., see Onuma 129 (1993) 706
Nakamura, M., S. Katsura, N. Makino, E. Ikeda, K. Suga and R. Hirano, Effect of substrate misorientation on tear-drop-like hillock defect densities in InP and GaInAsP grown by metalorganic chemical vapor deposition 129 (1993) 456
Nakanishi, Y., see Tatsuoka 129 (1993) 686
Nepijko, S.A., see Romanov 129 (1993) 691
Nikolov, V.S., see Shumov 129 (1993) 635
Nishihama, J., see Oda 129 (1993) 30
Noda, Y., see Tanaka 129 (1993) 683
Nørlund Christensen, A., Crystal growth and characterization of the transition metal silicides $MoSi_2$ and WSi_2 129 (1993) 266
Nyce, T.A., see Rosenberger 129 (1993) 1

Oda, K., T. Saito, J. Nishihama, T. Ishihara and M. Sato, Numerical simulation of melt growth: prediction of solid–liquid interface shape 129 (1993) 30
Odier, P., see Pellerin 129 (1993) 21
Offerman, H., see Tulke 129 (1993) 13
Ohtsuka, K., see Kaito 129 (1993) 367
Okada, S. and T. Lundström, Single crystal growth of V_2B_3 using the high-temperature aluminium solution method 129 (1993) 543
Okano, Y., see Pan 129 (1993) 365

Okomelchenko, I.A., see Kiselev 129 (1993) 163
Onuma, K., K. Tsukamoto and S. Nakadate, Application of real time phase shift interferometer to the measurement of concentration field 129 (1993) 706
Owczarek, I., see Sangwal 129 (1993) 640

Pain, G.N., see Gao 129 (1993) 134
Palosz, W. and H. Wiedemeier, Physical vapor transport of cadmium telluride in closed ampoules 129 (1993) 653
Pan, Shoukui, Y. Okano, S. Tsunekawa and T. Fukuda, Kyropoulos method for growth of nonlinear optical organic crystal ABP (4-aminobenzophenone) from the melt 129 (1993) 365
Pan, Z.X., see Xu 129 (1993) 666
Paskova, T., see Yakimova 129 (1993) 143
Patel, P.D., see Agarwal 129 (1993) 559
Patriarche, G., R. Triboulet, Y. Marfaing and J. Castaing, Imperfections in II–VI semiconductor layers epitaxially grown by organometallic chemical vapour deposition on GaAs 129 (1993) 375
Patterson, I.L.J., see Yates 129 (1993) 215
Pellerin, N., P. Odier and M. Gervais, Texturation of YBaCuO by laser zone melting 129 (1993) 21
Pogorelskii, Yu.V., see Karpov 129 (1993) 563
Polonsky, I.A., see Romanov 129 (1993) 691
Post, E. and V. Krämer, Crystal growth of $AgGaS_2$ by the Bridgman–Stockbarger and travelling heater methods 129 (1993) 485
Pourroy, G., see Brès 129 (1993) 149
Protzmann, H., see Zimmermann 129 (1993) 37

Radhakrishnan, S. and D.R. Saini, Polymer-induced crystallization of inorganic salts. II. PEO–$CaCl_2$, PEO–K_2CO_3 and PEO–$CaCO_3$ 129 (1993) 191
Richter, H., see Kühne 129 (1993) 321
Richter, W., see Zimmermann 129 (1993) 37
Ristorcelli, J.R. and J.L. Lumley, A second-order turbulence simulation of the Czochralski crystal growth melt: the buoyantly driven flow 129 (1993) 249
Rodríguez-Clemente, R., see Aspar 129 (1993) 56
Roentgen, P., see Catana 129 (1993) 779
Romanov, A.E., I.A. Polonsky, V.G. Gryaznov, S.A. Nepijko, T. Junghanns and N.I. Vitrykhovski, Voids and channels in pentagonal crystals 129 (1993) 691
Rosenberger, F., S.B. Howard, J.W. Sowers and T.A. Nyce, Temperature dependence of protein solubility – determination and application to crystallization in X-ray capillaries 129 (1993) 1
Rosenberger, F., see Monaco 129 (1993) 465
Rouzaud, A., J. Coméra, P. Contamin, B. Angelier, F. Herbillon and J.J. Favier, Interest of the thermoelectric measurements for crystal growth 129 (1993) 173
Rulmont, A., see Cloots 129 (1993) 394

Saini, D.R., see Radhakrishnan 129 (1993) 191
Saito, T., see Oda 129 (1993) 30
Saito, Y., see Kaito 129 (1993) 367
Sangwal, K. and I. Owczarek, On the formation of etch grooves at impurity striations and growth sector boundaries in crystals grown from solutions 129 (1993) 640
Sasaki, A., see Wang 129 (1993) 289
Sasaki, T., Surface morphology of MOVPE-grown GaN on (0001) sapphire 129 (1993) 81
Saska, M., G. Sgualdino, G. Vaccari, G. Mantovani and L. Zefiro, Faceting of spherical and cylindrical monocrystals of sucrose 129 (1993) 91
Sato, M., see Oda 129 (1993) 30
Saunders, B.V., see Murray 129 (1993) 70
Scheel, H.J., see Klemenz 129 (1993) 421
Schmid, H., see Kubel 129 (1993) 515
Scholl, S., see Waag 129 (1993) 243
Seilenthal, M., see Zimmermann 129 (1993) 582
Sgualdino, G., see Saska 129 (1993) 91
Shang, S.X., H. Wang and X.L. Sheng, Growth mechanism and crystal habit of $RBa_2Cu_3O_{7-x}$ (R = Y, Tm, Gd) single crystals 129 (1993) 411
Sheng, X.L., see Shang 129 (1993) 411
Sherwin, M.E., G.O. Munns, M.E. Elta, E.G. Woelk, S.B. Crary, F.L. Terry and G.I. Haddad, The optimization of $In_xGa_{1-x}As$ and InP growth conditions by CBE (E) 129 (1993) 794
Shi Rihua, see Wang 129 (1993) 774
Shih, I., see Yip 129 (1993) 102
Shih, I., see Shukri 129 (1993) 107
Shukri, Z.A., C.H. Champness and I. Shih, Boron nitride powder coating of ampoule for Bridgman-grown $CuInSe_2$ 129 (1993) 107
Shumov, D.P., M.P. Tarassov and V.S. Nikolov, Investigation of optical inhomogeneities in $KTiOPO_4$ (KTP) single crystals grown from high-temperature tungsten-containing solutions 129 (1993) 635
Škrtić, D. and H. Füredi-Milhofer, Influence of some aminoacids on the spontaneous precipitation of calcium oxalate from high ionic strength solutions 129 (1993) 449
Sowers, J.W., see Rosenberger 129 (1993) 1
Stekolnikov, A.V., see Cherepanova 129 (1993) 202
Stevenson, A.W., see Gao 129 (1993) 134
Stolz, W., see Zimmermann 129 (1993) 37
Suga, K., see Nakamura 129 (1993) 456

Takagashi, S., H. Yao and H. Mori, Origin and formation mechanism of elliptic-shaped surface defect on GaAs layers grown by molecular beam epitaxy 129 (1993) 443
Tanaka, U., T. Komori, N. Ishizawa, F. Marumo and Y. Noda, Growth of NiS_2 single crystals by sublimation under controlled sulfur pressure 129 (1993) 683
Tang, X., see Hageman 129 (1993) 281
Tarassov, M.P., see Shumov 129 (1993) 635
Tatsuoka, H., H. Kuwabara, Y. Nakanishi and H. Fujiyasu, CdTe (111) growth on misoriented Si (100) substrates by hot-wall epitaxy 129 (1993) 686
Terry, F.L., see Sherwin 129 (1993) 794
Tiller, W.A., see Yen 129 (1993) 224
Tiller, W.A. and S. Uda, Intrinsic $LiNbO_3$ melt species partitioning at the congruent melt composition. I. Static interface case 129 (1993) 328
Tiller, W.A. and S. Uda, Intrinsic $LiNbO_3$ melt species partitioning at the congruent melt composition. I. Dynamic interface case 129 (1993) 341
Triboulet, R., see Patriarche 129 (1993) 375
Tsukamoto, K., see Onuma 129 (1993) 706
Tsunekawa, S., see Pan 129 (1993) 365
Tulke, A. and H. Offermann, Measurement and discussion of potash alum crystal growth rate fluctuations and dispersion 129 (1993) 13

Uchida, T., N. Yokouchi, T. Miyamoto, F. Koyama and K. Iga, Some optical characteristics of beryllium-doped InP grown by chemical beam epitaxy (CBE) 129 (1993) 275
Uda, S., see Tiller 129 (1993) 328
Uda, S., see Tiller 129 (1993) 341

Vaccari, G., see Saska 129 (1993) 91
Van Tendeloo, G., see Cloots 129 (1993) 394
Velichko, A.A., see Kiselev 129 (1993) 163
Vilenkin, A.J. and A. Brokman, Geometric model of crystal growth between rigid walls. II. Anisotropic interface controlled normal and abnormal growth 129 (1993) 67
Vitrykhovski, N.I., see Romanov 129 (1993) 691
Von Schierstedt, K., see Waag 129 (1993) 243

Waag, A., S. Scholl, K. von Schierstedt, D. Hommel, G. Landwehr and G. Bilger, Bromine doping of CdTE and CdMnTe epitaxial layers grown by molecular beam epitaxy 129 (1993) 243
Wada, H. and K. Moriya, Observation of defects in semiconductor-on-insulator (SOI) wafers by a nondestructive bulk micro-defect analyzer 129 (1993) 405
Wakahara, A., see Wang 129 (1993) 289
Wang, H., see Shang 129 (1993) 411
Wang Qimin, Chen Qinggui, Shi Rihua, Zhu Weibing, Dong Qiwei and Dong Rongkang, Single-crystalline diamond film growth 129 (1993) 774
Wang, X.H., W. Zhu, J. von Windheim and J.T. Glass, Combustion growth of large diamond crystals 129 (1993) 45
Wang, X.L., A. Wakahara and A. Sasaki, OMVPE growth and characterization of $Al_xGa_{1-x}P$ $(0 \leqslant x \leqslant 1)$ using tertiary-butylphosphine 129 (1993) 289
Wanklyn, B.M., see Changkang 129 (1993) 239
Watanabe, T., see Kaito 129 (1993) 367
Werkmann, J., see Brès 129 (1993) 149
Wheeler, A.A., see Murray 129 (1993) 70
Weidemeier, H., see Palosz 129 (1993) 653
Wilkins, S.W., see Gao 129 (1993) 134
Williams, G.M., see Mackey 129 (1993) 269
Williams, J.O., see Yates 129 (1993) 215
Windheim, J. von, see Wang 129 (1993) 45
Woelk, E.G., see Sherwin 129 (1993) 794
Woodall, J.M., see Matyi 129 (1993) 719

Xiao, Q. and J.J. Derby, Bulk-flow versus thermal-capillary models for Czochralski growth of semiconductors 129 (1993) 593
Xie, Si-Shen, see Chang 129 (1993) 362
Xu, J.J. and Z.X. Pan, Interfacial wave theory of dendritic growth from a binary mixture: a comparison with experiments 129 (1993) 666
Xu, Zhengyi, Peiwen Ge, Chongru Huo and Zhenhe Zhu, Analyses of the characteristics of crystal growth from solution under microgravity. III. Effects of the orientation of microgravity 129 (1993) 506

Yakimova, R., T. Paskova and I. Ivanov, Layer quality of Sb-doped GaAs grown by metalorganic vapor phase epitaxy 129 (1993) 143
Yao, H., see Takagishi 129 (1993) 443
Yates, H.M., J.O. Williams, I.L.J. Patterson and D.J. Cole-Hamilton, Preparation and purification of dimethylzinc and the effect of iodine doping on the opto-electronic properties of epitaxial ZnSe layers grown by metalorganic chemical vapour deposition 129 (1993) 215
Yen, C.T. and W.A. Tiller, Incorporating convection into one-dimensional solute redistribution during crystal growth from the melt. II. The initial transient solution 129 (1993) 224
Yip, L.S., I. Shih and C.H. Champness, Method of avoiding ampoule adhesion of ingots in Bridgman growth of $CuInSe_2$ 129 (1993) 102
Yokouchi, N., see Uchida 129 (1993) 275

Yongle, Hu, see Changkang 129 (1993) 239
Yu, Yu-De, see Chang 129 (1993) 362

Zaumseil, P., Characterization of the perfection of $Si_{1-x}Ga_x$ layers on silicon by X-ray methods 129 (1993) 537
Zefiro, L., see Saska 129 (1993) 91
Zhokhov, A.A. and G.A. Emel'chenko, Growth of $YBa_2Cu_3O_{7-\delta}$ single crystals on seeds by a modified top seeded solution growth (TSSG) technique 129 (1993) 786
Zhou, Tang, see Chang 129 (1993) 362
Zhu, W., see Wang 129 (1993) 45
Zhu Weibing, see Wang 129 (1993) 774
Zhu, Zhenhe, see Xu 129 (1993) 506
Zimmermann, G., H. Protzmann, T. Marschner, O. Zsebök, W. Stolz, E.O. Göbel, P. Gimmnich, J. Lorberth, T. Filz, P. Kurpas and W. Richter, Amino-arsine and -phosphine compounds for the MOVPE of III–V semiconductors 129 (1993) 37
Zimmermann, H., U. Gösele, M. Seilenthal and P. Eichinger, Vacancy concentration wafer mapping in silicon 129 (1993) 582
Zinck, J.J., see Liu 129 (1993) 111
Zsebök, O., see Zimmermann 129 (1993) 37

Journal of Crystal Growth 129 (1993) 801–804
North-Holland

JOURNAL OF CRYSTAL GROWTH

Subject index

Alloys
– of III–V compounds 728
– of II–VI compounds 728
Aluminum
– gallium arsenide 37, 281, 532
– gallium phosphide 289
– nitride 56, 610, 621
4-Aminobenzophenone 365
Apparatus
– for solution growth
– – by temperature control
– – – of protein 1
– for thin film growth
– – by liquid phase electroepitaxy
– – – of semiconductors 429
– – by liquid phase epitaxy
– – – of high T_c superconductors 421
– for miscellaneous purposes
– – interferometry 706
– – solubility determination 1

Barium
– borate 371
Bismuth
– iron oxide 515

Cadmium
– manganese telluride 243
– mercury telluride 375
– telluride 111, 243, 375, 653, 686, 691
Calcite 789
Calcium
– carbonate 191, 789
– fluoride 163
– oxalate 449
– phosphate 149
Canavalin 1
Characterization methods
– by atomic absorption spectroscopy 233
– by atomic force microscopy 789
– by Auger electron spectroscopy 621
– by cathodoluminescence 269
– by chemical analysis 549
– by differential thermal analysis 485
– by electrical methods 37, 215, 243, 281, 289, 525, 559, 582, 786
– by electron diffraction 21, 774
– by electron microscopy 21, 45, 56, 81, 134, 143, 149, 163, 367, 375, 394, 405, 411, 443, 543, 610, 621, 635, 691, 699, 779
– by electron probe microanalysis 635
– by helium diffraction 416
– by interferometry 491
– by mass spectrometry 371
– by neutron 266
– by optical microscopy 37, 45, 91, 191, 269, 281, 289, 362, 365, 371, 394, 405, 421, 443, 449, 456, 465, 491, 515, 549, 571, 635, 640, 699, 774, 777, 783
– by optical properties 275
– by photoluminescence 215, 269, 275
– by Raman spectroscopy 45, 143
– by reflection high energy electron diffraction 686
– by secondary ion mass spectrometry 233, 375
– by Talystep surface profiling 421
– by thermoelectric measurement 173
– by thermogravimetric analysis 239, 449
– by transmission spectroscopy 362, 371, 375
– by X-ray methods 37, 56, 134, 191, 266, 365, 375, 394, 449, 485, 532, 537, 543, 559, 610, 635, 686, 719
Cobalt
– aluminum oxide 699
– oxide/zirconium oxide 699
Computer simulation
– of melt growth
– – by Bridgman–Stockbarger method 30, 70
– – by Czochralski method 249
– of solution growth under microgravity 506
– of tin–copper eutectic growth 549
Convection 70, 224, 249, 506, 549, 706
Copper
– indium selenide 102, 107
– oxide 239

Dendritic growth
– theory of 666
Device characterization
– quantum wells 532
– separation by implanted oxygen 405
Diamond 45, 774
Diffusion control
– in microgravity solution growth 506
– of calcium carbonate 191
Dissolution 465
Domains 515

Epitaxy, see Thin film growth
Etching
– chemical 443, 456, 515, 640, 777
– chemical, theory of 640
– thermal 465
Eutectic growth
– of cobalt oxide/aluminum oxide/zirconium oxide 699
– of cobalt oxide/zirconium oxide 699
– of tin copper 549

Gadolinium
– barium cuprate 411
Gallium
– aluminum arsenide 37
– arsenide 37, 134, 143, 281, 443, 719, 777
– indium arsenide 779
– indium arsenide phosphide 456, 779
– indium phosphide 456, 779, 783
– nitride 81
– phosphide 289
Germanium 525
– gallium 525

Heat flow control 119
Hydrodynamics, see Convection

Ice 491, 571
Impurity
– theory of 202
Indium
– gallium phosphide 783
– phosphide 37, 275, 456, 779
– selenide 312
Interface
– theory of 202

Kinetics
– of evaporation 571
– of growth 13, 91, 385, 416, 465, 789
– of interface control 67
– of nucleation 416
– of poisoning 789
– of surface growth 610

Lanthanum
– aluminate 362
Lithium
– niobate 328, 341
Lysozyme 1, 465

Melt growth technique
– by Bridgman–Stockbarger method
– – of copper indium selenide 102, 107
– – of silver gallium disulphide 485
– – of tin copper 549
– – theory of 30, 70
– by Czochralski method
– – of silicon 179
– – theory of 179, 249
– by floating zone method
– – of cobalt aluminum oxide 699
– – of cobalt oxide/zirconium oxide 699
– – of molybdenum silicide 266
– – of tungsten silicide 266
– – of yttrium barium cuprate 21
– – theory of 385, 593
– by Kyropoulos method
– – of 4-aminobenzophenone 365
– by traveling heater method
– – of silver gallium disulphide 485
– theory of 173, 224, 328, 341
Mercury
– cadmium telluride 233
Microgravity, growth under
– in solution 506
– theory of 70
Molybdenum
– selenide 559
– silicide 266
Morphological stability
– of diamond 45
– of ice 571
– of sucrose 91

Neodymium
– barium cuprate 421
Nickel
– sulphide 683
Nucleation
– of calcium carbonate 191
– of diamond 45
Numbers
– Grashof 30, 593
– Rayleigh 70
– Stanton 111

Palladium 416
Phase diagrams
– of copper oxide/barium oxide 239
– of lithium oxide/niobium oxide 328
– of neodymium barium cuprate 421
– of silver gallium disulphide/lead chloride 485
– of silver gallium disulphide/silver bromide 485
– of III–V compounds 563
– of yttrium barium cuprate 421
Potash
– alum 13
Potassium
– phosphate 640
– titanyl phosphate 635
Precursor
– for III–V alloys 728
– for II–VI alloys 728
Proteins 1

Quantum wells, see Device characterization

Silicon 179, 405, 582, 691
– germanium 321, 537
Silver
– gallium disulphide 485
Sodium
– chlorate 706
Solid growth technique
– of yttrium barium cuprate 394
Solution growth technique
– by flux method
– – of barium borate 371
– – of bismuth iron oxide 515
– – of copper oxide 239
– – of gadolinium barium cuprate 411
– – of potassium titanyl phosphate 635
– – of thulium barium cuprate 411
– – of vanadium boride 543
– – of yttrium barium cuprate 411, 786
– by gel method
– – of calcium carbonate 191
– by low temperature method
– – by lysozyme 465
– – of potash alum 13
– – of potassium phosphate 640
– – of sodium chlorate 706
– – of sucrose 91
– theory of 385, 506
Stefan problem or moving boundary problem 593
Step 571, 789
Strain 134, 686
Sucrose 91
Superconductivity materials, high T_c
– bulk
– – of YBCO 21
– film
– – of YBCO 394, 411, 421, 786
– – of NdBCO 421
Surface structure
– of calcium carbonate 789
– of ice 491, 571
– theory of 202

Thermodynamics
– of indium–selenium system, 297, 312
Thin film growth, epitaxy
– by atomic layer molecular beam epitaxy
– – of palladium 416
– by chemical beam epitaxy
– – of indium phosphide 275
– by flame
– – of diamond 45
– by hot wall epitaxy
– – of cadmium telluride 686
– by liquid phase electroepitaxy
– – of semiconductors 429
– by liquid phase epitaxy
– – of mercury cadmium telluride 233
– – of neodymium barium cuprate 421
– – of yttrium barium cuprate 421
– by molecular beam epitaxy
– – of aluminum gallium arsenide 532
– – of cadmium manganese telluride 243
– – of cadmium telluride 243
– – of calcium fluoride 163
– – of gallium arsenide 443, 719
– – of indium selenide 312
– – theory of 563
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of aluminum nitride 56
– – – of cadmium telluride 111
– – – of diamond 774
– – – of germanium 525
– – – of germanium gallium 525
– – – of silicon germanium 321
– – – theory of 111, 119
– – through evaporation and condensation
– – – of ice 491
– – through metalorganic chemical vapor deposition
– – – of aluminum gallium arsenide 281
– – – of aluminum gallium phosphide 289
– – – of aluminum nitride 610, 621
– – – of cadmium mercury telluride 375
– – – of cadmium telluride 375
– – – of gallium aluminum arsenide 37
– – – of gallium arsenide 37, 134, 143, 281
– – – of gallium indium arsenide 779
– – – of gallium indium arsenide phosphide 779
– – – of gallium indium phosphide 456, 783
– – – of gallium nitride 81
– – – of indium phosphide 37, 456, 779
– – – of III–V alloys 728
– – – of II–VI alloys 728
– – – of zinc selenide 215
– – – of zinc selenide telluride 629
– – – of zinc sulphide selenide 629
– – – of zinc sulphide telluride 629
– – – of zinc telluride 629
– – – theory of 629
Thulium
– barium cuprate 411
Tin
– copper 549
– sulphide 367
Tungsten
– silicide 266

Vanadium
– boride 543
Vapor growth technique
– by chemical transport
– – of molybdenum selenide 559
– by evaporation and condensation
– – of cadmium telluride 653, 691

– – of nickel sulphide 683
– – of silicon 691
Vapor–liquid–solid growth
– of tin sulphide 367
Vapor–solid growth
– of yttrium barium sulphur oxide 394

Whisker growth
– of cadmium telluride 691
– of silicon 691

Yttrium
– barium cuprate 21, 394, 411, 421, 786
– barium sulphur oxide 394
– orthoaluminate 269

Zinc
– selenide 215
– selenide telluride 629
– sulphide selenide 629
– sulphide telluride 629
– telluride 375, 629